

HIGH VOLTAGE POWER TRANSISTORS

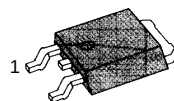
DPAK FOR SURFACE MOUNT APPLICATIONS

- Lead Formed for Surface Mount Applications (No Suffix)
- Straight Lead (" - I " Suffix)

ABSOLUTE MAXIMUM RATINGS

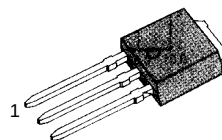
Characteristic	Symbol	Rating	Unit
Collector Base Voltage	V_{CBO}	300	V
Collector Emitter Voltage	V_{CEO}	300	V
Emitter Base Voltage	V_{EBO}	3	V
Collector Current (DC)	I_C	0.5	A
Collector Current (Pulse)	I_C	0.75	A
Collector Dissipation ($T_A=25^\circ\text{C}$)	P_C	1.56	W
Collector Dissipation ($T_C=25^\circ\text{C}$)	P_C	15	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-65 ~ 150	$^\circ\text{C}$

D-PAK



1. Base 2. Collector 3. Emitter

I-PAK



1. Base 2. Collector 3. Emitter

ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$)

Characteristic	Symbol	Test Conditions	Min	Max	Unit
* Collector Emitter Sustaining Voltage	$V_{CEO} \text{ (sus)}$	$I_C = 1\text{mA}, I_B = 0$	300		V
Collector Cutoff Current	I_{CEO}	$V_{CB} = 300\text{V}, I_E = 0$		0.1	mA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 3\text{V}, I_C = 0$		0.1	mA
* DC Current Gain	h_{FE}	$V_{CE} = 10\text{V}, I_C = 50\text{mA}$	30	240	

* Pulse Test : $PW \leq 300\mu\text{A}$, Duty Cycle $\leq 2\%$

KSH340

NPN EPITAXIAL SILICON TRANSISTOR

